

## Electrostatic Discharged Protection Devices (ESD) Data Sheet

### Description

The UAD20C03L02 is an ultra low capacitance TVS array designed to Protect high speed data interfaces. This series has been specifically Designed to protect sensitive components which are connected to data an transmission lines from overvoltage caused by electrostatic discharge (ESD),cable discharge events (CDE) and lightning.

The unique design incorporates surge rated, low capacitance steering diodes and a TVS diode in a single package. During transient conditions, the steering diodes direct the transient current to ground. The internal TVS diode clamps the transient voltage to a safe level. The ultra low capacitance array configuration allows the user to protect up to the high speed data lines. These devices are in a signal package, RoHS/WEEE compliant, DFN2010 package. It measures 2.0x1.0x0.8mm.

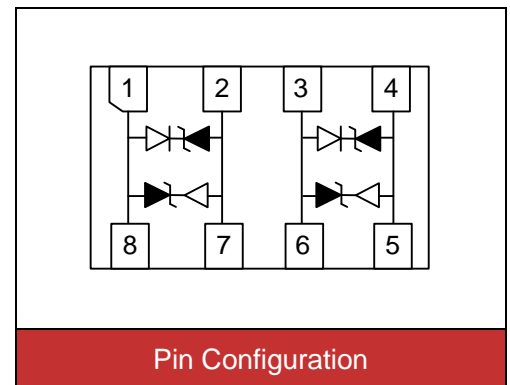


Contact :  $\pm 20\text{kV}$   
Air :  $\pm 20\text{kV}$



### Features

- IEC61000-4-2 ESD 20kV Air, 20kV contact compliance
- DFN2010 (2.0x1.0x0.5mm) surface mount package
- Protects two I/O lines
- Working voltage: 3V
- Low leakage current
- Low operating and clamping voltages
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020
- Marking: B X32



### Applications

- USB 2.0 interface
- 10/100/1000 Ethernet
- LAN/WAN Equipment
- Security Cameras
- Industrial Controls
- Peripherals
- Handhelds and notebooks
- Digital cameras

## Maximum Ratings

Rating	Symbol	Value	Unit
Peak Pulse Current (tp=8/20μs)	$I_{PP}$	3	A
ESD voltage (Contact discharge)	$V_{ESD}$	±20	kV
ESD voltage (Air discharge)		±20	
Storage & operating temperature range	$T_{STG}, T_J$	-55~+150	°C

## Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				3	V
Reverse breakdown voltage	$V_{BR}$	$I_{BR}=1\text{mA}$	3.5			V
Reverse leakage current	$I_R$	$V_R=3.0\text{V}$			1	μA
Clamping voltage (tp=8/20μs)	$V_C$	$I_{PP}=3.0\text{A}$		15		V
Off state junction capacitance	$C_J$	0Vdc, f=1MHz		3		pF

## Typical Characteristics Curves

Figure 1. Capacitance vs. Bias Voltage

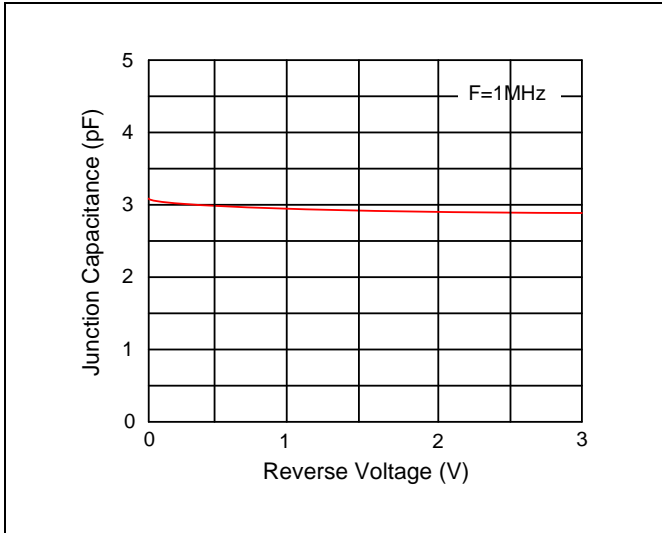


Figure 2. Insertion Loss (S21) I/O to GND

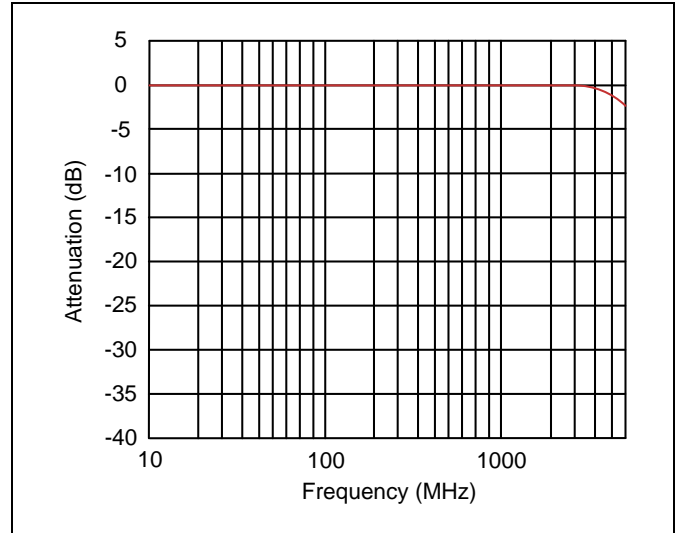


Figure 3. Pulse Waveform

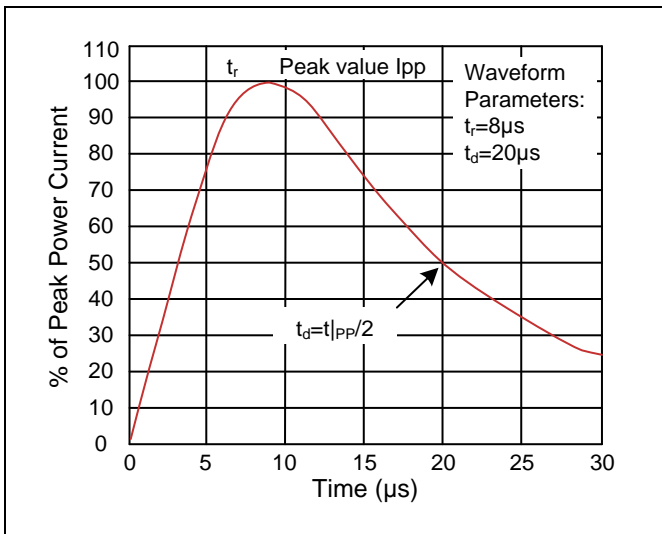
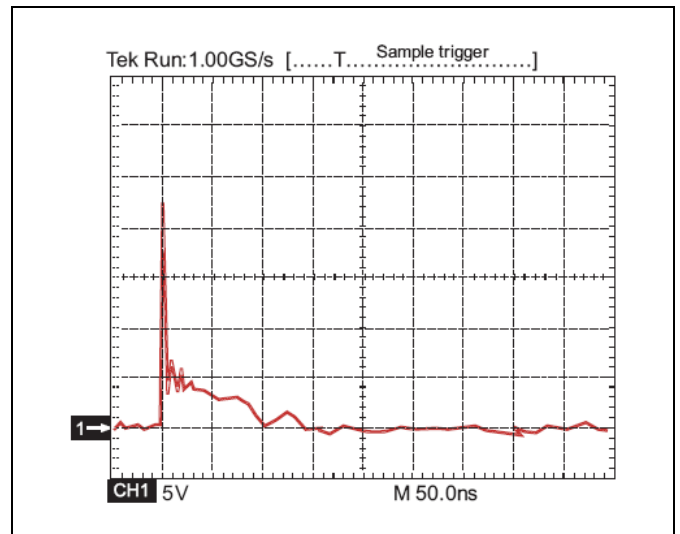
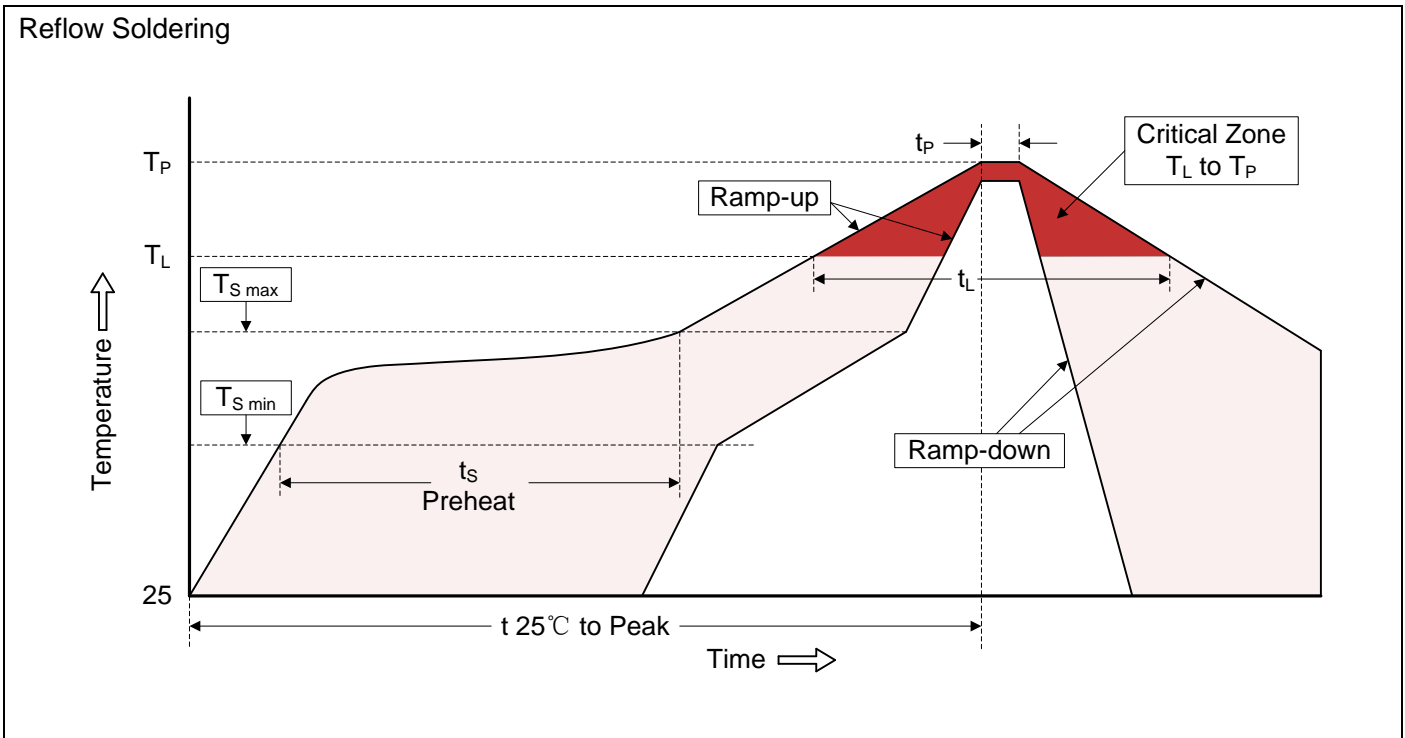


Figure 4. ESD Clamping (8kV Contact IEC61000-4-2)



**Recommended Soldering Conditions**



**Recommended Conditions**

Profile Feature	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	3°C/second max.
Preheat -Temperature Min ( $T_{S\ min}$ ) -Temperature Max ( $T_{S\ max}$ ) -Time (min to max) ( $t_s$ )	150°C 200°C 60-180 seconds
$T_{S\ max}$ to $T_L$ -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature ( $T_L$ ) -Time ( $t_L$ )	217°C 60-150 seconds
Peak Temperature ( $T_P$ )	260°C
Time within 5°C of actual Peak Temperature ( $t_p$ )	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

**Dimensions (DFN-2010)**

	Dimension						
	Symbol	Millimeters			Inches		
		Min.	Nom	Max.	Min.	Nom	Max.
A	0.450	0.500	0.550	0.018	0.020	0.022	
A1	0.000	0.021	0.046	0.000	0.001	0.002	
A2	0.110REF			0.005REF			
b	0.200	0.250	0.300	0.008	0.010	0.012	
D	1.924	2.000	2.076	0.076	0.079	0.082	
E	0.924	1.000	1.076	0.036	0.039	0.042	
e	0.500TYP			0.020TYP			
L	0.274	0.350	0.426	0.011	0.014	0.017	
K	0.200MIN			0.008MIN			

**Packaging**

<p><b>Tape</b></p>	Symbol	Dimension (mm)
	A0	1.16±0.05
	B0	2.20±0.05
	K0	0.55±0.05
	P0	4.00±0.10
	P1	4.00±0.10
	P2	2.00±0.05
	T	0.20±0.02
	E	1.75±0.10
	F	3.50±0.05
	D0	1.55±0.05
	D1	0.6±0.10
	W	8.0+0.1/-0.05
	D	Φ178.0±2.0
	D1	60
D2	Φ13.0±0.5	
W1	8.4±1.5	
Quantity: 3000PCS		